



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	40 V
D	18 A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	14 mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	19 mohm
100% EAS Tested	
100% V_{DS} Tested	

General Description

Excellent package for heat dissipation
High density cell design for low $R_{DS(ON)}$
Moisture Sensitivity Level 1
Epoxy Meets UL 94 V-0 Flammability Rating
Halogen Free

Applications

High current load applications
Load switching
Hard switched and high frequency circuits
Uninterruptible power supply



YJG18N04A

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250$	40			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V, V_{GS}=0V$	$T_J=25$		1	
			$T_J=150$		100	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=20V, V_{DS}=0V$				



Typical Performance Characteristics

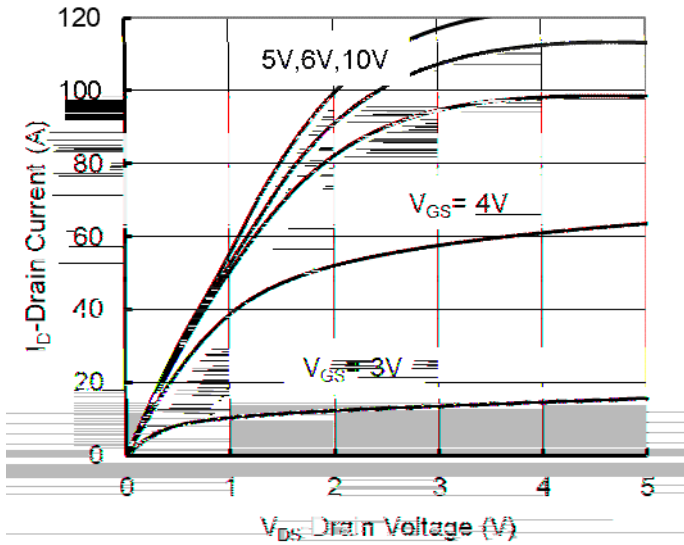


Figure 1. Output Characteristics

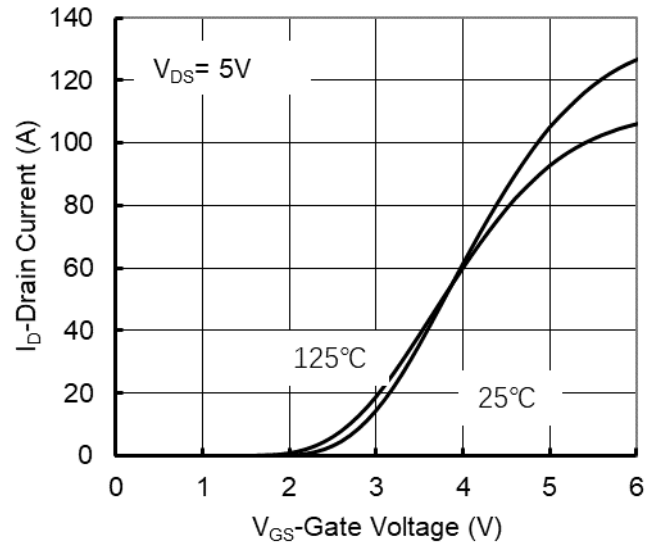


Figure 2. Transfer Characteristics

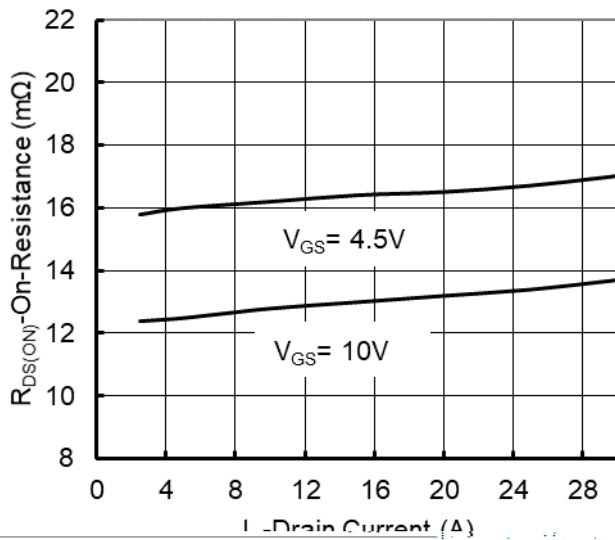


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

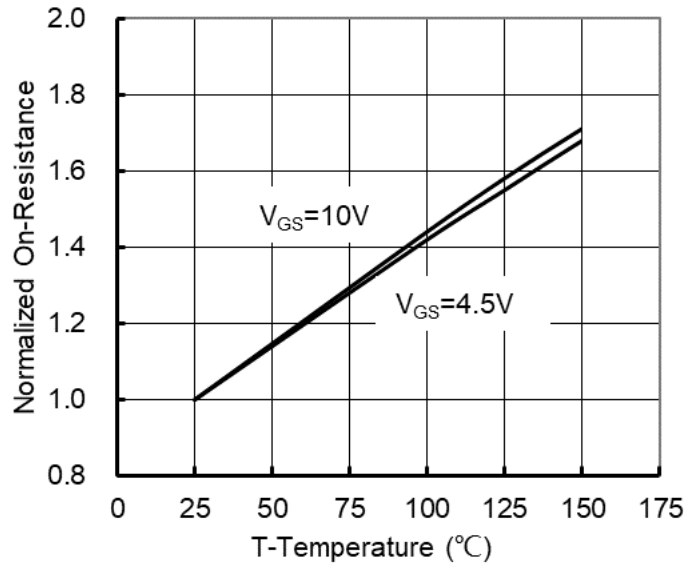


Figure 4. On-Resistance vs. Junction Temperature

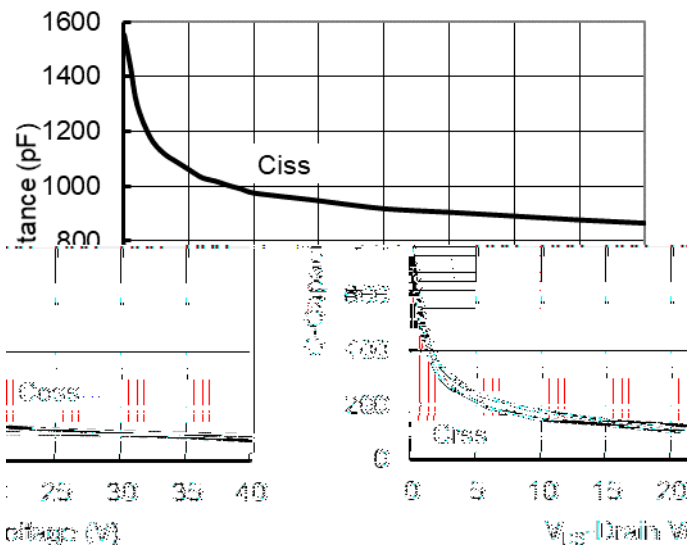


Figure 5. Capacitance Characteristics

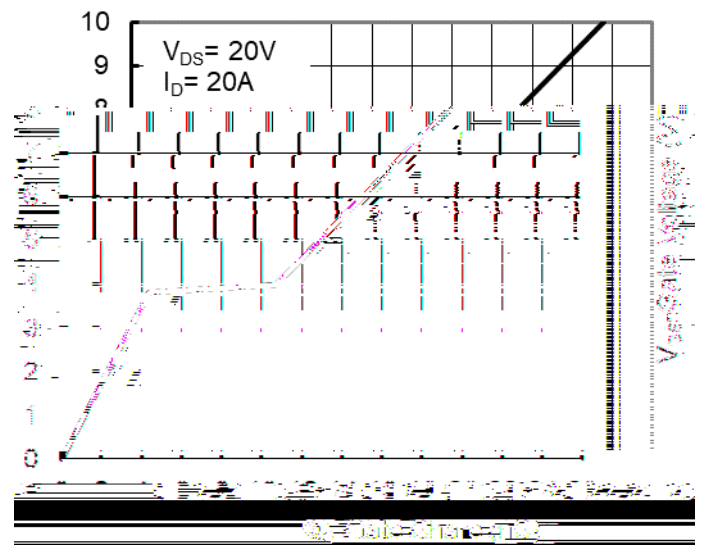


Figure 6. Gate Charge

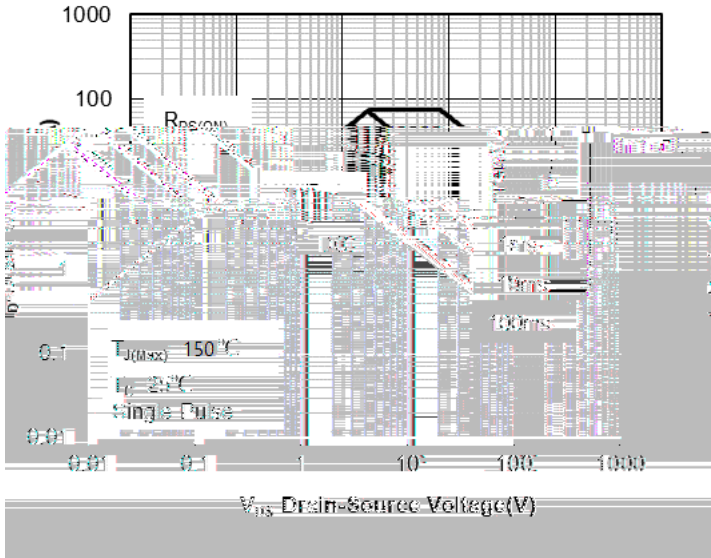


Figure 7. Safe Operation Area

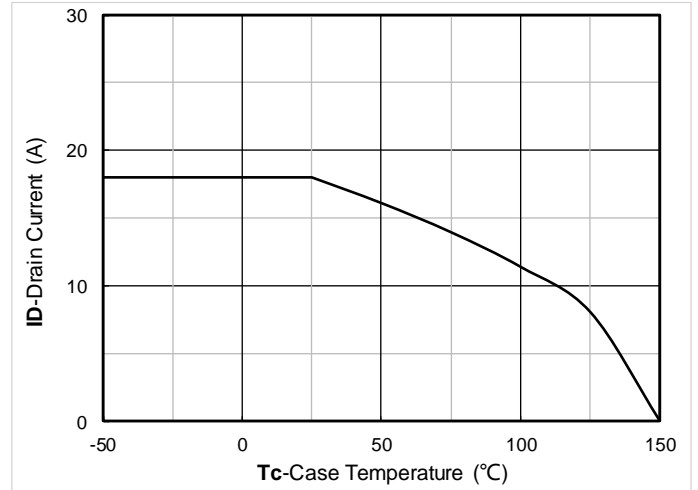


Figure 8. Maximum Continuous Drain Current vs Case Temperature

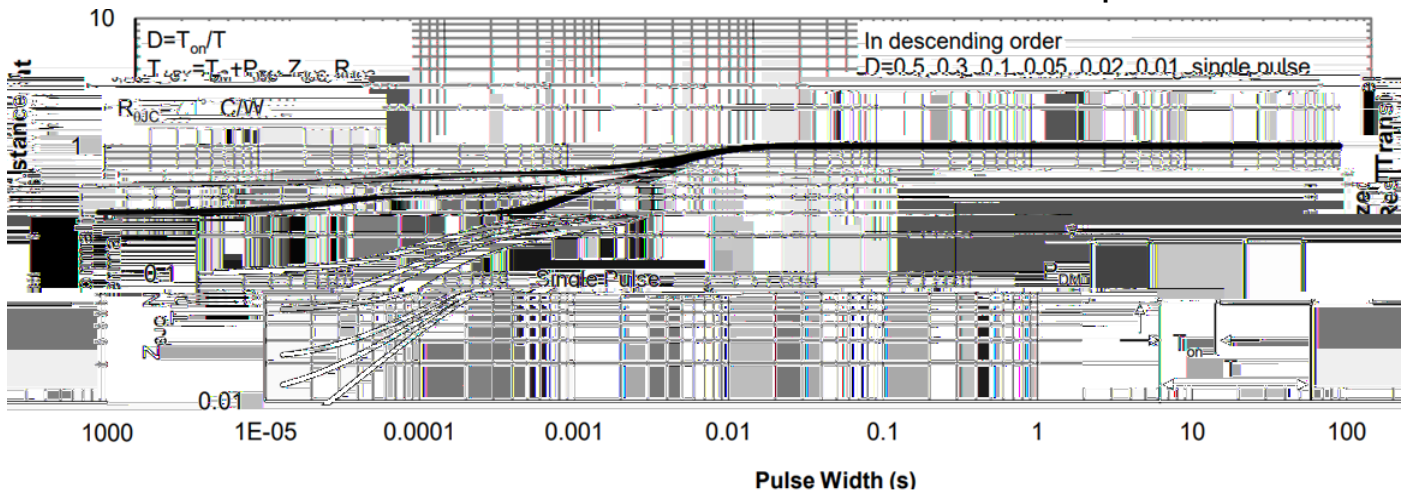
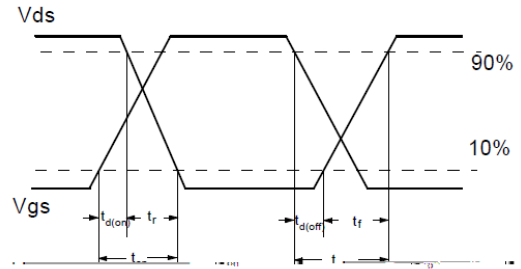
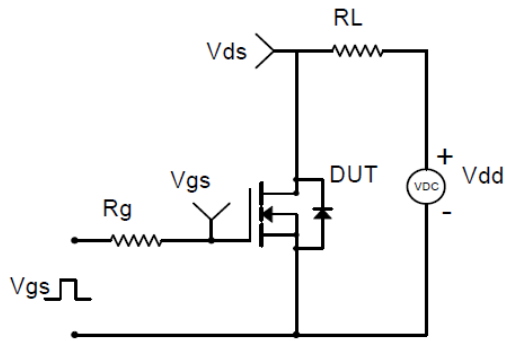
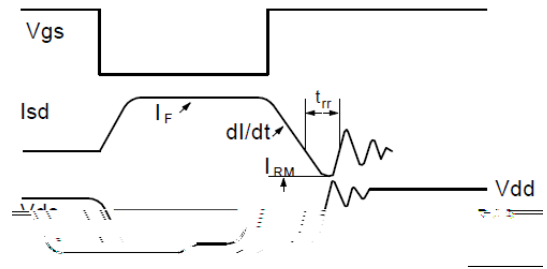
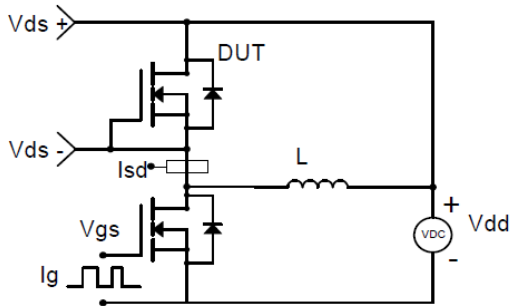


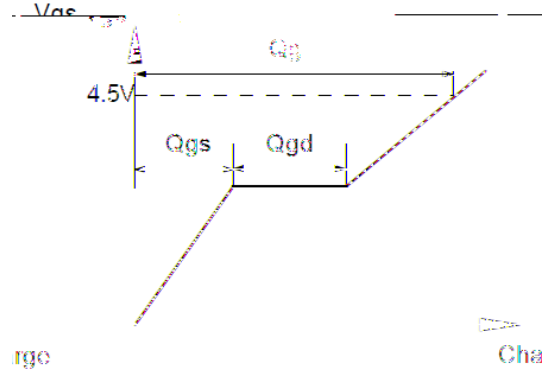
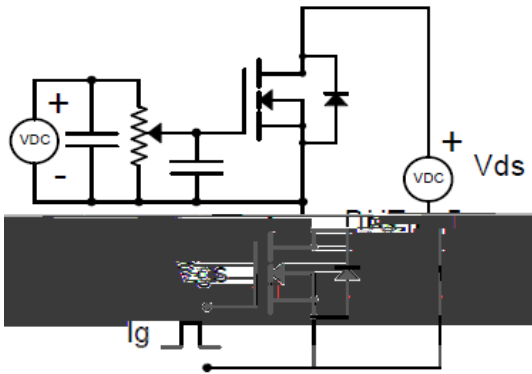
Figure 9. Normalized Maximum Transient Thermal Impedance



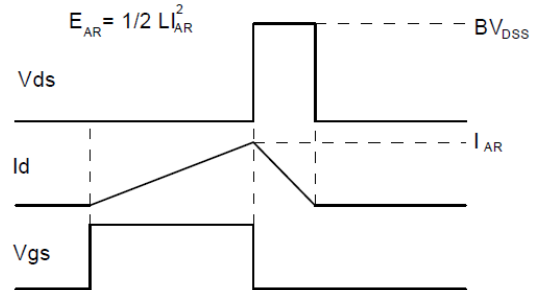
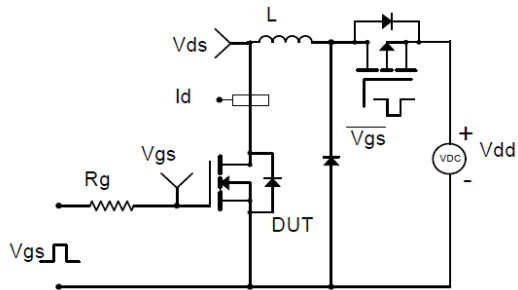
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

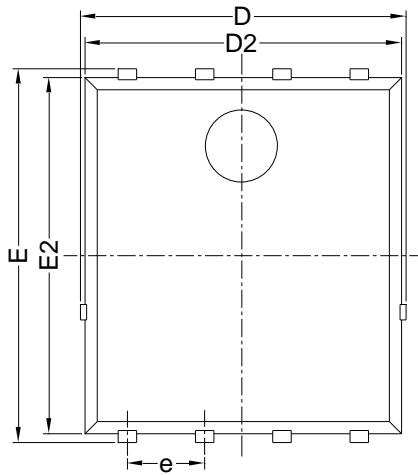


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms

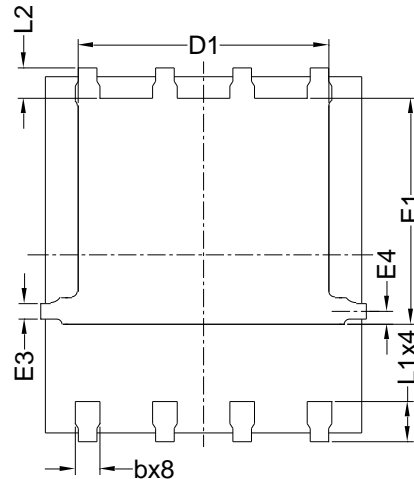


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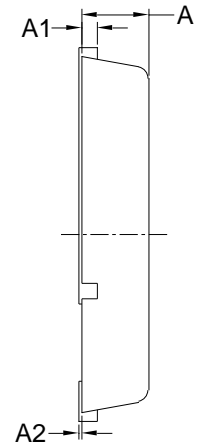
PDFN5060-8L-B-1.1MM Package Information



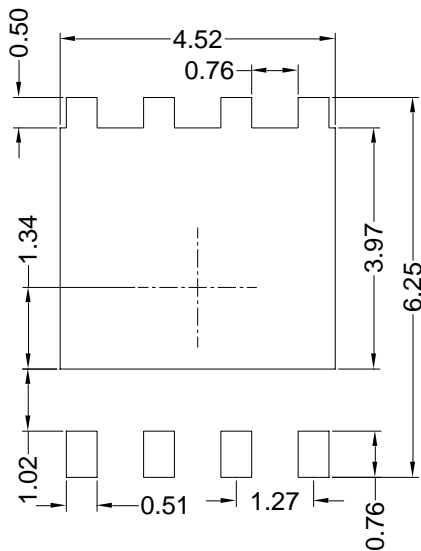
Top View



Bottom View



Side View



Suggested Solder Pad Layout
Top View

SYMBOL	MILLIMETER		
	MIN	NOM	MAX
D	5.15	5.35	5.55
E	5.95	6.15	6.35
A	1.00	1.10	1.20
A1	0.254 BSC		
A2			0.10
D1	3.92	4.12	4.32
E1	3.52	3.72	3.92
D2	5.00	5.20	5.40
E2	5.66	5.86	6.06
E3	0.254 REF		
E4	0.21 REF		
L1	0.56	0.66	0.76
L2	0.50 BSC		
b	0.31	0.41	0.51
e	1.27 BSC		

Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.10 mm.
3. The pad layout is for reference purposes only.



YJG18N04A

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